ORIENTATION OF THE MAGNETIC MOMENTS IN PERPENDICULAR ANISOTROPIC THIN FILMS BY HALL EFFECT

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1. Introduction

As we known, in magnetic thin films, there always exists the ordinary and extraordinary Hall effect. The former one is due to Lorentz force and the latter one is proportional directly to sample's magnetization [1]. The extraordinary Hall effect (EHE) has been recognized as an useful tool for measuring the magnetic hysteresis M(H) curves of magnetic film having perpendicular anisotropy [2].

Generally, the EHE voltage is governed by the perpendicular component of the magnetization. The final (saturation) magnetization state is, however, determined by the applied field direction. So that the EHE voltage can increase or decrease depending on the relative of the initial magnetic moment direction with respect to the applied magnetic field one. As a consequence, the EHE voltage vs. field curve is expected to be analyzed to determine the magnetic moment direction. This problem is tackled in this paper. This idea is realized for TerfecoHan film.

2. Experiments

The films with thickness of 570 nm were deposited on glass substrates using rfsputtering technique at room temperature. A vibrating sample magnetometer was used to determine the magnetization M. Domain structure was studied using MFM with magnetic tip that were magnetized perpendicular to the sample plane. The conversion electron Mossbauer spectra (CEMS) at room temperature were recorded using a conventional spectrometer equipped with a home-made helium-methane proportional counter. The Hall effect measurement has been carried out at room temperature by the standard dc four probe method on the square samples of 4×4 mm². The longitudinal Hall voltage V_u was measured in direction perpendicular to the currents I, as a function of the applied magnetic field as well as the field direction. α is defined to be the angle between the film plane and field direction.

3. Results and discussions

The perpendicular magnetic anisotropy of the investigated film is clearly evidenced by Magnetic Force Microscopy (MFM) in Fig. 1. At zero fields, MFM image allows us to see a complex structure in which there exists the interlacement of bright and dark color together corresponding to that domains with different polarity. The alternating perpendicular magnetization component gave rise to the contrast of the MFM images since MFM measures force gradient acting on the tip due to the perpendicular component of the surface field. These two stripes were found to have almost the same size and posses equal areas. When having a magnetic field applied on this sample, the magnetization process makes domain structure changed (domain width, geometrical type) until the sample approached saturation state.

This magnetic structure is also confirmed by Conversion Electron Mossbauer Spectral (CEMS) in Fig. 2. The result turns out from fit of the Mossbauer Spectrum that the average angle β between TbFeCo magnetic moments and the film normal is equal to 75°. This demonstrates that the magnetization of TerfecoHan film seems to orientate perpendicular to film plane.

The normalized $V_{\rm H}/V_{\rm Hass}$ and $M/M_{\rm max}$ curves measured in direction perpendicular to the film plane are presented in Fig. 3. Note that the sign of Hall coefficient isn't taken into account. The results showed that the $V_{\rm H}({\rm H})$ curve and the ${\rm M}({\rm H})$ curve are well coincidental. The agreement between two experiments is rather good for indicating the coercive force H, as well as hysteresis curves. However, there still exist the small discrepancies due to the mechanical hysteresis. This is understood as follows. According to the theoretical model proposed by Mc Guire et al, ρ_n closely relates to



Fig.1. The MFM image of magnetic TerfecoHan film

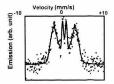


Fig.2. The Mössbauer spectra obtained at room temperature

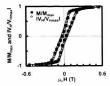
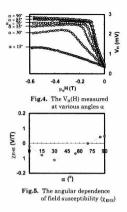


Fig.3. The M/M_{max} and V_B/V_{Hmax} curves of TerfecoHan film

magnetization mechanism [1]. In this case of TerfeoHan with perpendicular magnetic anisotropy, the rotation of magnetic moments in applied field leads to change $V_{\rm H}$. The large change of $\rho_{\rm H}$ at low field proves the contribution of perpendicular magnetization component to the longitudinal Hall voltage.

In high fields, the saturation tendency is not obtained for both EHE and M curves. In both case, one observes a rather large EHE and M slope (χ_{EHE} and χ_{M} in Fig. 4). As α decreases, χ_{EHE} initially decreases, annuls at $\alpha_{-} = 70^{\circ}$ and finally changes in sign (see Fig. 5). At the angle $\alpha_m = 70^{\circ}$, only existing a sufficient magnetic field of 0.15 T. all magnetic moments immediately arrange parallel to the field direction. The saturation process reaches completely at low field, while that requires a larger magnetic field for the case of other angles a. We assume that the direction of magnetic field coincides with that of magnetization in this case. The value of $\alpha_m = 70^{\circ}$



corresponds to $\beta = 30^{\circ}$. This value is somewhat higher than that obtained for the CEMS analysis. The accuracy of these two methods should be verified. However it allows us to explain experimental observation, in particular, the change in sign of $\gamma_{\rm mis}$.

In summary, the perpendicular magnetic anisotropy of the TerfecoHan thin film is well evidenced by means of MFM, VSM as well as EHE experiments. Thank to that, the EHE magnetometry is proposed to be used to study magnetization process. Moreover, EHE investigations are quite possible to determine the magnetic moment orientation in the magnetic films having perpendicular anisotropy.

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